

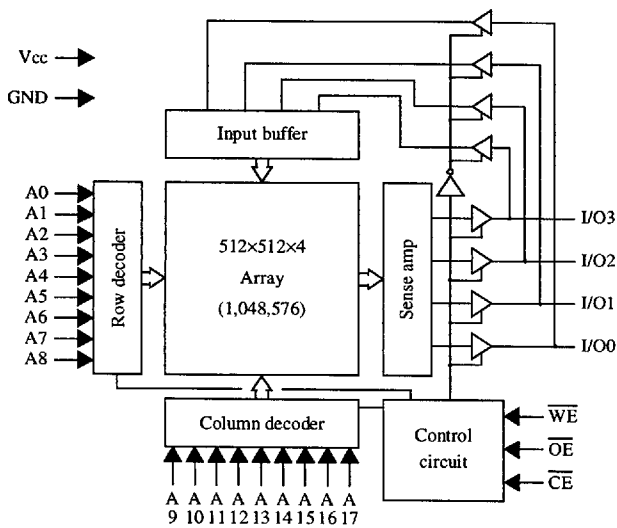


256K×4 CMOS SRAM

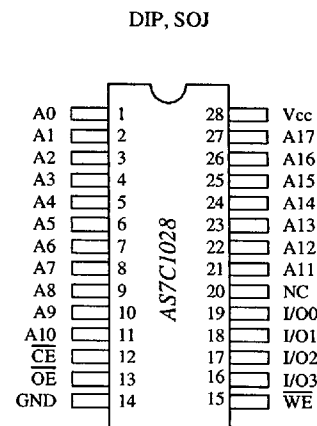
Features

- Organization: 262,144 words × 4 bits
- High speed
 - 12/15/20/25/35 ns address access time
 - 4/4/5/6/8 ns output enable access time
- Low power consumption
 - Active: 660 mW max (15 ns cycle)
 - Standby: 27.5 mW max, CMOS I/O
5.5 mW max, CMOS I/O, L version
 - Very low DC component in active power
- 2.0V data retention (L version)
- Equal access and cycle times
- Easy memory expansion with \overline{CE} and \overline{OE} inputs
- TTL-compatible, three-state I/O
- 28-pin JEDEC standard packages
 - 300 mil PDIP and SOJ
 - 400 mil PDIP and SOJ
- ESD protection > 2000 volts
- Latch-up current > 200 mA

Logic block diagram



Pin arrangement



Selection guide

	7C1028-12	7C1028-15	7C1028-20	7C1028-25	7C1028-35	Unit
Maximum address access time	12	15	20	25	35	ns
Maximum output enable access time	4	4	5	6	8	ns
Maximum operating current	130	120	110	100	80	mA
Maximum CMOS standby current	5.0	5.0	5.0	5.0	5.0	mA
	L	1.0	1.0	1.0	1.0	mA

Shaded areas contain advance information.



Functional description

The AS7C1028 is a high performance CMOS 1,048,576-bit Static Random Access Memory (SRAM) organized as 262,144 words × 4 bits. It is designed for memory applications where fast data access, low power, and simple interfacing are desired.

Equal address access and cycle times (t_{AA} , t_{RC} , t_{WC}) of 12/15/20/25/35 ns with output enable access times (t_{OE}) of 4/4/5/6/8 ns are ideal for high performance applications. A chip enable (\overline{CE}) input permits easy memory expansion with multiple-bank memory organizations.

When \overline{CE} is HIGH the device enters standby mode. The standard AS7C1028 is guaranteed not to exceed 27.5 mW power consumption in standby mode; the L version is guaranteed not to exceed 5.5 mW, and typically requires only 800 μ W. The L version also offers 2.0V data retention, with maximum power consumption in this mode of 600 μ W.

A write cycle is accomplished by asserting chip enable (\overline{CE}) and write enable (\overline{WE}) LOW. Data on the input pins I/O0-I/O3 is written on the rising edge of \overline{WE} (write cycle 1) or \overline{CE} (write cycle 2). To avoid bus contention, external devices should drive I/O pins only after outputs have been disabled with output enable (\overline{OE}) or write enable (\overline{WE}).

A read cycle is accomplished by asserting chip enable (\overline{CE}) and output enable (\overline{OE}) LOW, with write enable (\overline{WE}) HIGH. The chip drives I/O pins with the data word referenced by the input address. When chip enable or output enable is HIGH, or write enable is LOW, output drivers stay in high-impedance mode.

All chip inputs and outputs are TTL-compatible, and operation is from a single 5V supply. The AS7C1028 is packaged in high volume industry standard packages.

Absolute maximum ratings

Parameter	Symbol	Min	Max	Unit
Voltage on any pin relative to GND	V_t	-0.5	+7.0	V
Power dissipation	P_D	—	1.0	W
Storage temperature (plastic)	T_{stg}	-55	+150	°C
Temperature under bias	T_{bias}	-10	+85	°C
DC output current	I_{out}	—	20	mA

Stresses greater than those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions outside those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Truth table

\overline{CE}	\overline{WE}	\overline{OE}	Data	Mode
H	X	X	High Z	Standby (I_{SB} , I_{SB1})
L	H	H	High Z	Output Disable
L	H	L	D_{out}	Read
L	L	X	D_{in}	Write

Key: X = Don't Care, L = LOW, H = HIGH

Recommended operating conditions

Parameter	Symbol	Min	Typ	$(T_a = 0^\circ\text{C to } +70^\circ\text{C})$	
				Max	Unit
Supply voltage	V_{CC}	4.5	5.0	5.5	V
	GND	0.0	0.0	0.0	V
Input voltage	V_{IH}	2.2	—	$V_{CC}+1$	V
	V_{IL}	-0.5 [†]	—	0.8	V

[†] V_{IL} min = -3.0V for pulse width less than $t_{RC}/2$



DC operating characteristics¹

(V_{CC} = 5V±10%, GND = 0V, T_a = 0°C to +70°C)

Parameter	Symbol	Test Conditions	-12		-15		-20		-25		-35		Unit	
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max		
Input leakage current	I _{LI}	V _{CC} = Max, V _{in} = GND to V _{CC}	-	1	-	1	-	1	-	1	-	1	µA	
Output leakage current	I _{LO}	$\overline{CE} = V_{IH}$, V _{CC} = Max, V _{out} = GND to V _{CC}	-	1	-	1	-	1	-	1	-	1	µA	
Operating power supply current	I _{CC}	$\overline{CE} = V_{IL}$, f = f _{max} , I _{out} = 0 mA	L	-	130	-	120	-	110	-	100	-	80	mA
				-	125	-	115	-	105	-	95	-	75	mA
Standby power supply current	I _{SB}	$\overline{CE} = V_{IH}$, f = f _{max}	L	-	50	-	40	-	40	-	35	-	30	mA
				-	45	-	35	-	35	-	30	-	25	mA
Output voltage	V _{OL} V _{OH}	I _{OL} = 8 mA, V _{CC} = Min I _{OH} = -4 mA, V _{CC} = Min	L	-	0.4	-	0.4	-	0.4	-	0.4	-	0.4	V
				2.4	-	2.4	-	2.4	-	2.4	-	2.4	-	V

Capacitance²

(f = 1 MHz, T_a = Room Temperature, V_{CC} = 5V)

Parameter	Symbol	Signals	Test Conditions	Max	Unit
Input capacitance	C _{IN}	A, \overline{CE} , \overline{WE} , \overline{OE}	V _{in} = 0V	5	pF
I/O capacitance	C _{I/O}	I/O	V _{in} = V _{out} = 0V	7	pF

Key to switching waveforms

Rising input

Falling input

Undefined output/don't care

Read cycle^{3,9}

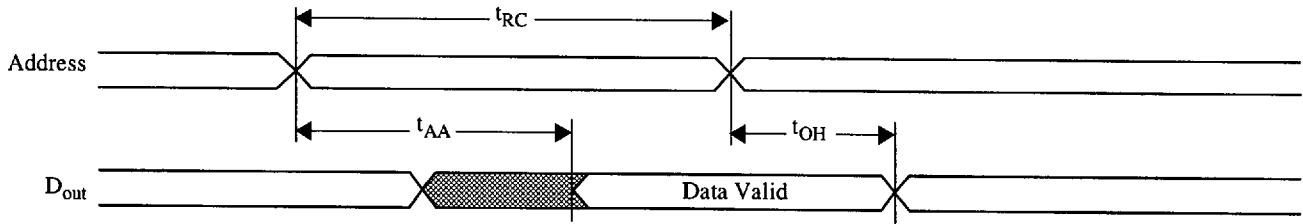
(V_{CC} = 5V±10%, GND = 0V, T_a = 0°C to +70°C)

Parameter	Symbol	-12		-15		-20		-25		-35		Unit	Notes
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max		
Read cycle time	t _{RC}	12	-	15	-	20	-	25	-	35	-	ns	
Address access time	t _{AA}	-	12	-	15	-	20	-	25	-	35	ns	3
Chip enable (\overline{CE}) access time	t _{ACE}	-	12	-	15	-	20	-	25	-	35	ns	3
Output enable (\overline{OE}) access time	t _{OE}	-	3	-	4	-	5	-	6	-	8	ns	
Output hold From address change	t _{OH}	3	-	3	-	3	-	3	-	3	-	ns	5
Chip enable to output in Low Z	t _{CLZ}	3	-	3	-	3	-	3	-	3	-	ns	4, 5
Chip disable to output in High Z	t _{CHZ}	-	3	-	4	-	5	-	6	-	8	ns	4, 5
Output enable to output in Low Z	t _{OLZ}	0	-	0	-	0	-	0	-	0	-	ns	4, 5
Output disable to output in High Z	t _{OHZ}	-	3	-	4	-	5	-	6	-	8	ns	4, 5
Chip enable to power up time	t _{PU}	0	-	0	-	0	-	0	-	0	-	ns	4, 5
Chip Disable to power down time	t _{PD}	-	12	-	15	-	20	-	25	-	35	ns	4, 5



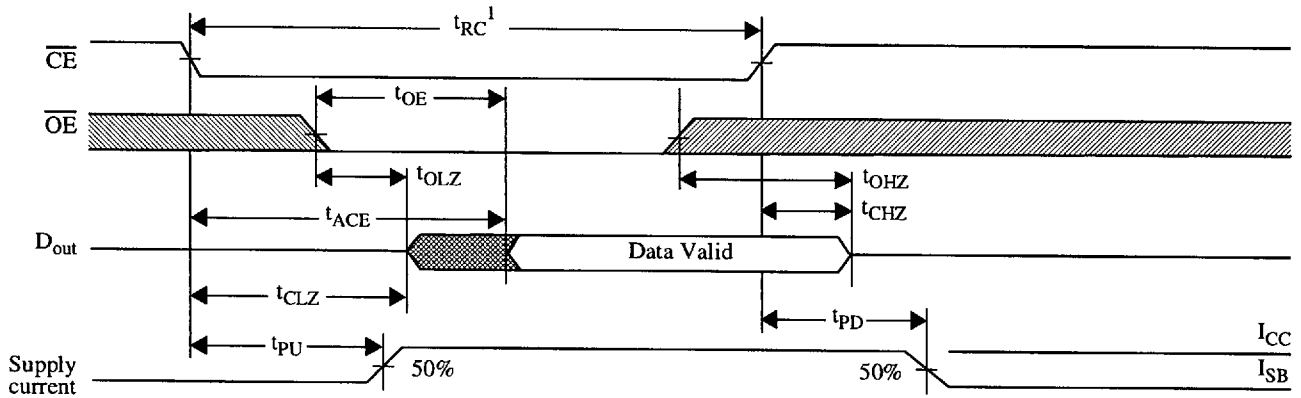
Read waveform 1^{3,6,7,9}

Address controlled



Read waveform 2^{3,6,8,9}

CE controlled



Write cycle¹¹

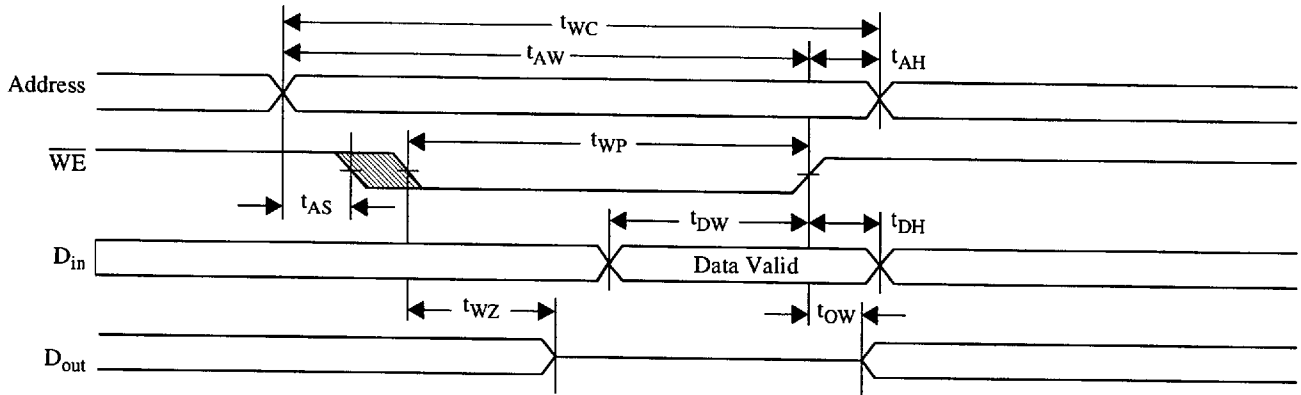
($V_{CC} = 5V \pm 10\%$, $GND = 0V$, $T_a = 0^\circ C$ to $+70^\circ C$)

Parameter	Symbol	-12		-15		-20		-25		-35		Unit	Notes
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max		
Write cycle time	t_{WC}	12	—	15	—	20	—	20	—	30	—	ns	
Chip enable to write end	t_{CW}	10	—	10	—	12	—	15	—	20	—	ns	
Address setup to write end	t_{AW}	10	—	10	—	12	—	15	—	20	—	ns	
Address setup time	t_{AS}	0	—	0	—	0	—	0	—	0	—	ns	
Write pulse width	t_{WP}	8	—	9	—	12	—	15	—	17	—	ns	
Address hold from end of write	t_{AH}	0	—	0	—	0	—	0	—	0	—	ns	
Data valid to write end	t_{DW}	8	—	9	—	10	—	10	—	15	—	ns	
Data hold time	t_{DH}	0	—	0	—	0	—	0	—	0	—	ns	4, 5
Write enable to output in High Z	t_{WZ}	—	5	—	5	—	5	—	5	—	5	ns	4, 5
Output active from write end	t_{OW}	3	—	3	—	3	—	3	—	3	—	ns	4, 5



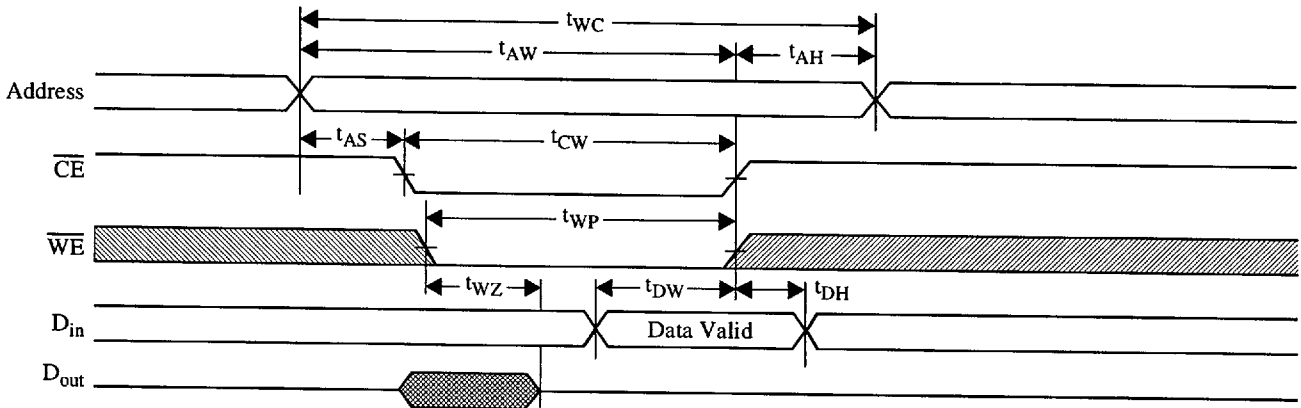
Write waveform 1^{10,11}

\overline{WE} controlled



Write waveform 2^{10,11}

\overline{CE} controlled



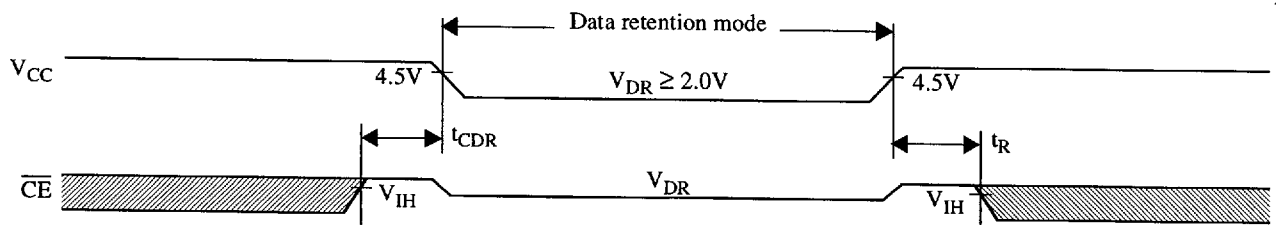
Data retention characteristics

L version only

Parameter	Symbol	Test Conditions	Min	Max	Unit
V_{CC} for data retention	V_{DR}	$V_{CC} = 2.0V$	2.0	—	V
Data retention current	I_{CCDR}	$\overline{CE} \geq V_{CC} - 0.2V$	—	300	μA
Chip deselect to data retention time	t_{CDR}	$V_{in} \geq V_{CC} - 0.2V$ or $V_{in} \leq 0.2V$	0	—	ns
Operation recovery time	t_R		t_{RC}	—	ns
Input leakage current	$ I_{LI} $		—	1	μA

Data retention waveform

L version only





AC test conditions

- Output load: see Figure B, except for t_{CLZ} and t_{CHZ} see Figure C.
- Input pulse level: GND to 3.0V. See Figure A.
- Input rise and fall times: 5 ns. See Figure A.
- Input and output timing reference levels: 1.5V.

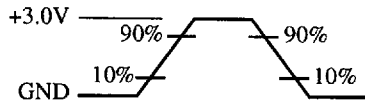


Figure A: Input Waveform

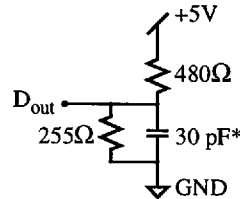


Figure B: Output Load

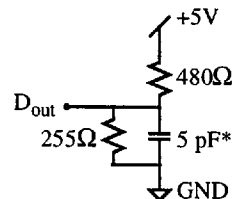
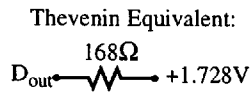


Figure C: Output Load for t_{CLZ} , t_{CHZ}

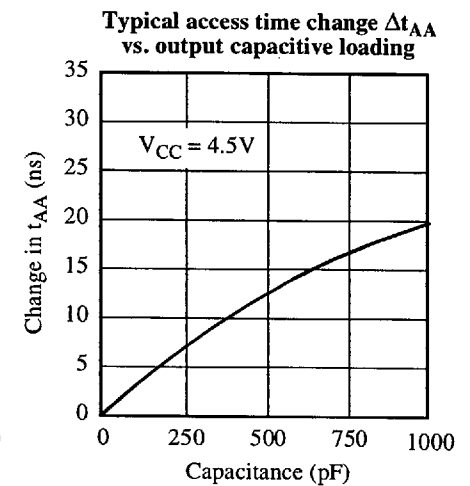
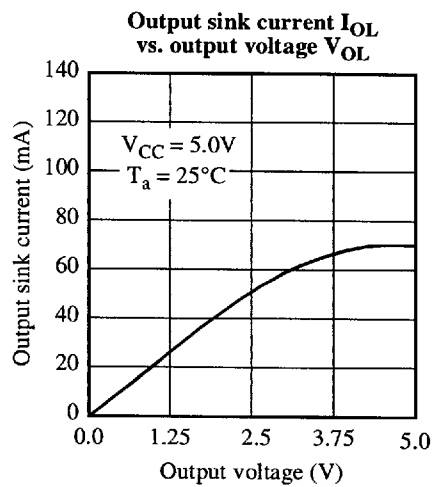
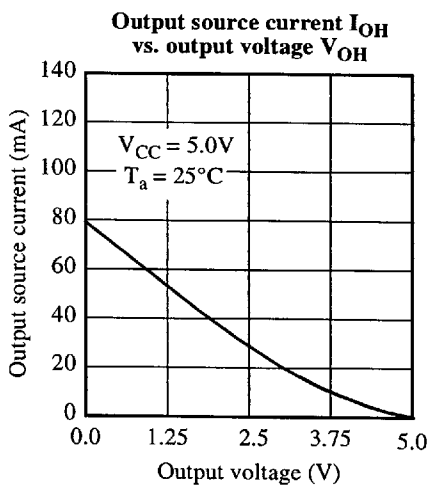
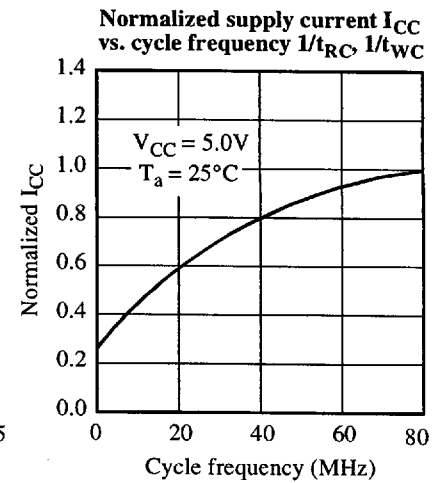
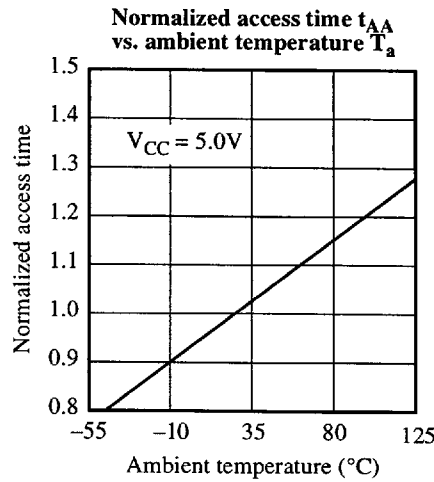
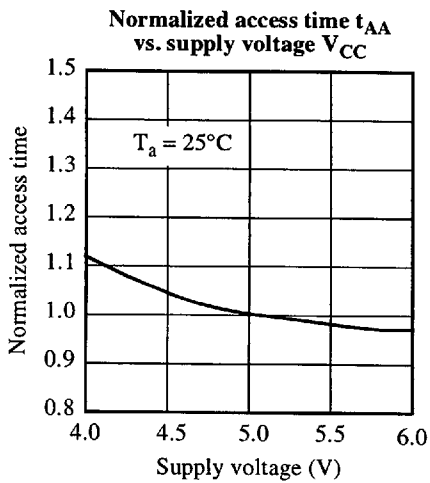
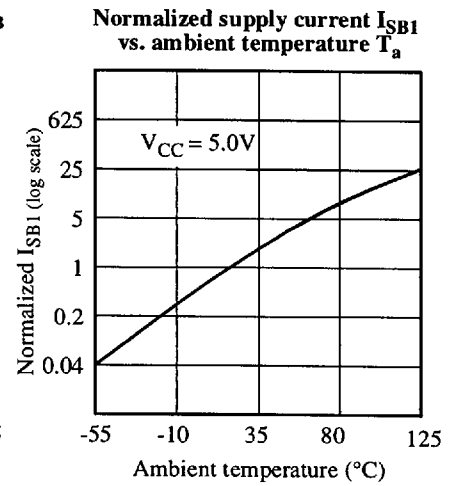
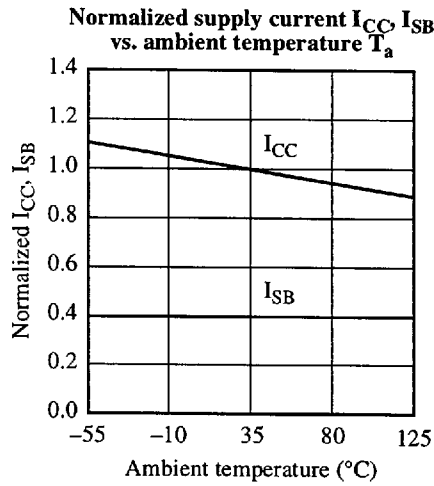
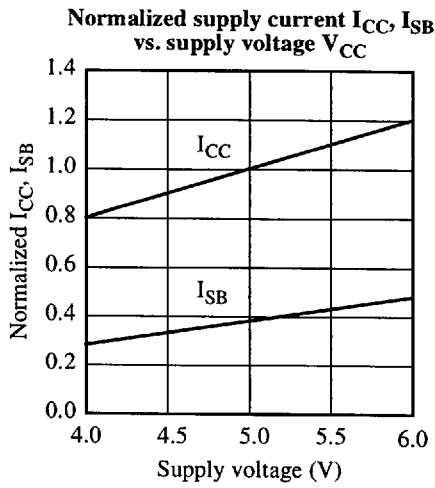
*including scope and jig capacitance

Notes

- 1 During V_{CC} power-up, a pull-up resistor to V_{CC} on \overline{CE} is required to meet I_{SB} specification.
- 2 This parameter is sampled and not 100% tested.
- 3 For test conditions, see AC Test Conditions, Figures A, B, C.
- 4 t_{CLZ} and t_{CHZ} are specified with $CL = 5pF$ as in Figure C. Transition is measured $\pm 500mV$ from steady-state voltage.
- 5 This parameter is guaranteed but not tested.
- 6 \overline{WE} is HIGH for read cycle.
- 7 \overline{CE} and \overline{OE} are LOW for read cycle.
- 8 Address valid prior to or coincident with \overline{CE} transition LOW.
- 9 All read cycle timings are referenced from the last valid address to the first transitioning address.
- 10 \overline{CE} or \overline{WE} must be HIGH during address transitions.
- 11 All write cycle timings are referenced from the last valid address to the first transitioning address.



Typical DC and AC characteristics





Ordering codes

Package \ Access Time	12 ns	15 ns	20 ns	25 ns	35 ns
Plastic DIP, 300 mil	AS7C1028-12TPC AS7C1028L-12TPC	AS7C1028-15TPC AS7C1028L-15TPC	AS7C1028-20TPC AS7C1028L-20TPC	AS7C1028-25TPC AS7C1028L-25TPC	AS7C1028-35TPC AS7C1028L-35TPC
Plastic DIP, 400 mil	AS7C1028-12PC AS7C1028L-12PC	AS7C1028-15PC AS7C1028L-15PC	AS7C1028-20PC AS7C1028L-20PC	AS7C1028-25PC AS7C1028L-25PC	AS7C1028-35PC AS7C1028L-35PC
Plastic SOJ, 300 mil	AS7C1028-12TJC AS7C1028L-12TJC	AS7C1028-15TJC AS7C1028L-15TJC	AS7C1028-20TJC AS7C1028L-20TJC	AS7C1028-25TJC AS7C1028L-25TJC	AS7C1028-35TJC AS7C1028L-35TJC
Plastic SOJ, 400 mil	AS7C1028-12JC AS7C1028L-12JC	AS7C1028-15JC AS7C1028L-15JC	AS7C1028-20JC AS7C1028L-20JC	AS7C1028-25JC AS7C1028L-25JC	AS7C1028-35JC AS7C1028L-35JC

Shaded areas contain advance information.

Part numbering system

AS7C	1028	X	-XX	X	C	
DOMESTIC REPS	Device name	Blank L	= Standard power = Low power	Access time	Package: TP = PDIP 300 mil P = PDIP 400 mil SOJ = SOJ 300 mil SOJ = SOJ 400 mil	Commercial temperature range. 0°C to 70°C
ALABAMA	CenTech (816) 358-8100					
ARKANSAS	Southern States Marketing (214) 238-7500					
CALIFORNIA	North Brooks Technical (415) 960-3880 LA Area Competitive Tech. (714) 450-0170 San Diego ATS (619) 634-1488					
COLORADO	Technology Sales (303) 692-8835					
CONNECTICUT	Kitchen & Kutchin (203) 239-0212					
DELAWARE	Electro Tech (610) 272-2125					
FLORIDA	Micro-Electronic Comp. Deerfield Beach (954) 426-8944 Orlando (407) 682-9602 Tampa (813) 393-5011					
GEORGIA	Concord Component (770) 416-9597					
HAWAII	Brooks Technical (415) 960-3880					
IDAHO	ES/Chase (503) 684-8500					
ILLINOIS	North El-Mech (312) 794-9100 South CenTech (314) 291-4230					
INDIANA	CC Electro Sales (317) 921-5000					
KENTUCKY	CC Electro Sales (317) 921-5000					
LOUISIANA	Southern States Marketing (214) 238-7500					
MAINE	Kitchen & Kutchin (617) 229-2660					
MARYLAND	Chesapeake Tech. (301) 236-0530					
MASSACHUSETTS	Kitchen & Kutchin (617) 229-2660					
MICHIGAN	Enco Group (810) 338-8600					
MINNESOTA	D. A. Case Associates (612) 831-6777					
MISSOURI	CenTech (816) 358-8100					
MISSISSIPPI	Concord Component (205) 772-8883					
MONTANA	ES/Chase (503) 684-8500					
NEBRASKA	CenTech (816) 358-8100					
NEVADA	Brooks Technical (415) 960-3880					
NEW HAMPSHIRE	Kitchen & Kutchin (617) 229-2660					
NEW JERSEY	ERA Associates (800) 645-5500					
NEW YORK	NYC ERA Associates (516) 543-0510 Upstate Tri-Tech Rochester (716) 385-6500 Binghamton (607) 722-3580					
NORTH CAROLINA	Concord Component (919) 846-3441					
NORTH DAKOTA	D. A. Case Associates (612) 831-6777					
OHIO	Midwest Marketing Assoc. Lyndhurst (216) 381-8575 Dayton (513) 433-2511					
OKLAHOMA	Southern States Marketing (214) 238-7500					
OREGON	ES/Chase (503) 684-8500					
PENNSYLVANIA	East Electro Tech (610) 272-2125 West Midwest Marketing (216) 381-8575					
RHODE ISLAND	Kitchen & Kutchin (617) 229-2660					
SOUTH CAROLINA	Concord Component (919) 846-3441					
SOUTH DAKOTA	D. A. Case Associates (612) 831-6777					
TENNESSEE	Concord Component (205) 772-8883					
TEXAS	Southern States Marketing Austin (512) 835-5822 Dallas (214) 238-7500 Houston (713) 895-8533					
UTAH	Charles Fields & Assoc. (801) 299-8228					
VERMONT	Kitchen & Kutchin (617) 229-2660					
VIRGINIA	Chesapeake Tech. (301) 236-0530					
WASHINGTON	ES/Chase (206) 823-9535					
WEST VIRGINIA	Chesapeake Tech. (301) 236-0530					
WISCONSIN	D. A. Case Associates (612) 831-6777					
WYOMING	Technology Sales (303) 692-8835					
INTERNATIONAL REPS						
AUSTRALIA	Dingley R&D Electronics +61-3-9558-0444 Bayswater ACD +61-3-9762-7644					
CANADA	J-Squared Technologies Ottawa (613) 592-9540 Toronto (905) 672-2030 Montreal (514) 747-1211 Vancouver (604) 473-4666 Calgary (403) 291-6755					
EUROPE	Brilcomp Sales Munich, Germany +49-894488496 Athlissimos, France +33-1-69387678 interACTIVE Great Britain, Ireland +44-1773-740263 Ramtec Int'l B.V. Holland, Spain, Italy, Belgium, Hungary, Russia +31-2526-21222					
HONG KONG	Eastele Technology +852-2798-8860					
INDIA	Priya Electronics, Inc. San Jose, CA USA (408) 954-1866					
ISRAEL	Eldis Technology +972-9-562-666					
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KOREA	FM Korea +822-596-3880 fm@kmet.co.kr					
MALAYSIA	Exer Technologies +60-4-657-9592					
PUERTO RICO	Micro-Electronic Comp. (787) 746-9897					
SINGAPORE	Exer Technologies +65-749-1349					
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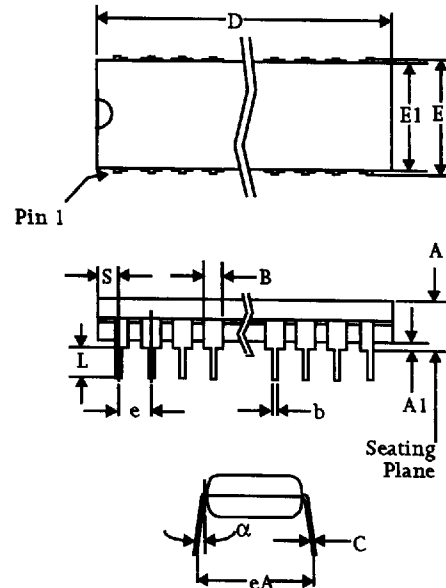
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8



Plastic dual in-line package (PDIP)

	20-pin 300 mil		28-pin 300 mil		32-pin 300 mil		32-pin 400 mil	
	Min	Max	Min	Max	Min	Max	Min	Max
A	-	0.175	-	0.175	-	0.180	-	0.200
A1	0.010	-	0.010	-	0.015	-	0.015	-
B	0.046	0.054	0.058	0.064	0.045	0.055	0.045	0.065
b	0.018	0.024	0.016	0.022	0.015	0.021	0.014	0.022
C	0.008	0.014	0.008	0.014	0.008	0.012	0.009	0.015
D	-	0.980	-	1.400	-	1.571	-	1.620
E	0.290	0.310	0.295	0.320	0.300	0.325	0.390	0.425
E1	0.263	0.293	0.278	0.298	0.280	0.295	0.340	0.390
e	0.100 BSC		0.100 BSC		0.100 BSC		0.100 BSC	
eA	0.310	0.350	0.330	0.370	0.330	0.370	0.430	0.470
L	0.110	0.130	0.120	0.140	0.110	0.142	0.118	0.162
α	0°	15°	0°	15°	0°	15°	0°	15°
S	-	0.040	-	0.055	-	0.043	-	0.065



Dimensions in inches

Plastic small outline J-bend (SOJ)

	20/26-pin 300 mil		28-pin 300 mil		32-pin 300 mil		28-pin 400 mil		32-pin 400 mil		36-pin 400 mil		40-pin 400 mil		42-pin 400 mil		44-pin 400 mil	
	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max
A	-	0.140	-	0.140	-	0.145	0.132	0.146	-	0.145	-	-	-	0.145	0.128	0.148	0.128	0.148
A1	0.020	-	0.025	-	0.025	-	0.062	-	0.025	-	-	-	0.025	-	0.025	-	0.025	-
A2	0.095	0.105	0.095	0.105	0.086	0.105	0.105	115	0.086	0.115	0.102 NOM		0.086	0.115	1.105	1.115	1.105	1.115
B	0.025	0.032	0.028 TYP		0.026	0.032	0.024	0.032	0.026	0.032	-	0.032	0.026	0.032	0.026	0.032	0.026	0.032
b	0.016	0.022	0.018 TYP		0.014	0.020	0.013	0.021	0.015	0.020	0.013	0.021	0.015	0.022	0.015	0.020	0.015	0.020
c	0.008	0.014	0.010 TYP		0.006	0.013	0.005	0.012	0.007	0.013	-	-	0.007	0.014	0.007	0.013	0.007	0.013
D	-	0.686	-	0.730	0.820	0.830	0.720	0.729	0.820	0.830	0.920	0.930	1.015	1.035	1.070	1.080	1.120	1.130
E	0.327	0.347	0.327	0.347	0.330	0.340	0.430	0.440	0.435	0.445	0.350	0.390	0.435	0.445	0.370 NOM		0.370 NOM	
E1	0.295	0.305	0.295	0.305	0.292	0.305	0.395	0.405	0.395	0.405	0.400 NOM		0.395	0.405	0.395	0.405	0.395	0.405
E2	0.245	0.285	0.245	0.285	0.250	0.275	0.354	0.378	0.360	0.380	0.435	0.445	0.348	0.390	0.435	0.445	0.435	0.445
e	0.050 BSC		0.050 BSC		0.050 BSC		0.050 BSC		0.050 BSC		0.045	0.055	0.050 BSC		0.050 NOM		0.050 NOM	

Dimensions in inches

